

Title (en)

METHOD FOR MAKING MONOCRYSTALLINE SILICON ISLANDS ELECTRICALLY ISOLATED FROM EACH OTHER

Publication

EP 0197078 B1 19900307 (FR)

Application

EP 85904827 A 19851001

Priority

FR 8415302 A 19841005

Abstract (en)

[origin: WO8602198A1] The method for making monocrystalline silicon islands electrically isolated from each other comprises the formation of patterns (17) of insulating material on a monocrystalline silicon substrate (12), the deposition on the structure assembly of an amorphous or polycrystalline silicon film (26), the coating of the silicon film (26) with an encapsulating material layer (28), the thermotreatment of the resulting structure in order to vertically embed into the substrate (12) the insulating material patterns (17) and to form on top of those depressed patterns (17) a monocrystalline silicon layer (33), the suppression of the encapsulating material layer (28), and the etching of the obtained monocrystalline silicon layer (33) so as to form said islands (24).

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IPC 8 full level

H01L 21/20 (2006.01); **H01L 21/762** (2006.01)

CPC (source: EP US)

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Citation (examination)

- EP 0141506 A2 19850515 - AMERICAN TELEPHONE & TELEGRAPH [US]
- IBM Technical Disclosure Bulletin, volume 24, No. 78, December 1981, New York, (US) V.J. Silvestri: "Silicon-Silicon Dioxide-Silicon structures", pages 3689-3690

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